Form PTO 1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO.		SERIAL NO.		
(Modified)		PATENT AND TRAD	EMARK OFFICE	310114US2PCT	10/551,702			
				APPLICANT				
LIST OF	REFE	RENCES CITED BY API	PLICANT	Haruki TODA				
				FILING DATE		GROUP		
				September 30, 2005		2815		
				U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS		
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		OTHER RE	FERENCES (Including Author, Title, Date, Pertiner	nt Pages, et	.c.)	I.	
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	AZ				Additional References sheet(s) attached			
Examiner					Date Considered			
*Examiner: Init conformance a	ial if re	eference is considered, v t considered. Include co	whether or not by of this form	citation is in conformance with MPEP 6 with next communication to applicant.	09; Draw lin	e through	citation	if not in